

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&R	L1	497	(438/261,591).CCLS.	USPAT; US-PGPUB	2002/10/08 14:30
2	BRS	L2	72	1 and @pd>20020404	USPAT; US-PGPUB	2002/10/08 14:39
3	IS&R	L3	1	("20020009852").PN.	USPAT; US-PGPUB	2002/10/08 14:43
4	BRS	L4	20074	carrier adj gas	USPAT; US-PGPUB	2002/10/08 14:44
5	BRS	L5	357	4 same (anneal\$3)	USPAT; US-PGPUB	2002/10/08 14:48
6	BRS	L6	4	5 same ono	USPAT; US-PGPUB	2002/10/08 14:45
7	BRS	L7	170	4 same ((ar or argon) and (o or oxygen) and (n or nirogen))	USPAT; US-PGPUB	2002/10/08 14:49

	Document ID	Pages	Title	Current OR	Current XRef	Inventor
1	US 6368398 B2	11	Method of depositing films by using carboxylate complexes	106/287.1 8	106/287.19; 427/126.1; 427/126.3; 427/226; 427/384; 427/96; 438/240; 438/3; 438/754; 438/758	Vaartstra, Brian A.
2	US 20020009852 A1	30	Method of manufacturing semiconductor device	438/261	257/E29.165; 257/E29.306; 438/763	Kobayashi, Takashi et al.